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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

Cautions

Keep safety first in your circuit designs!

1. Renesas Technology Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.

Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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2SJ575

Silicon P Channel MOS FET High Speed Switching

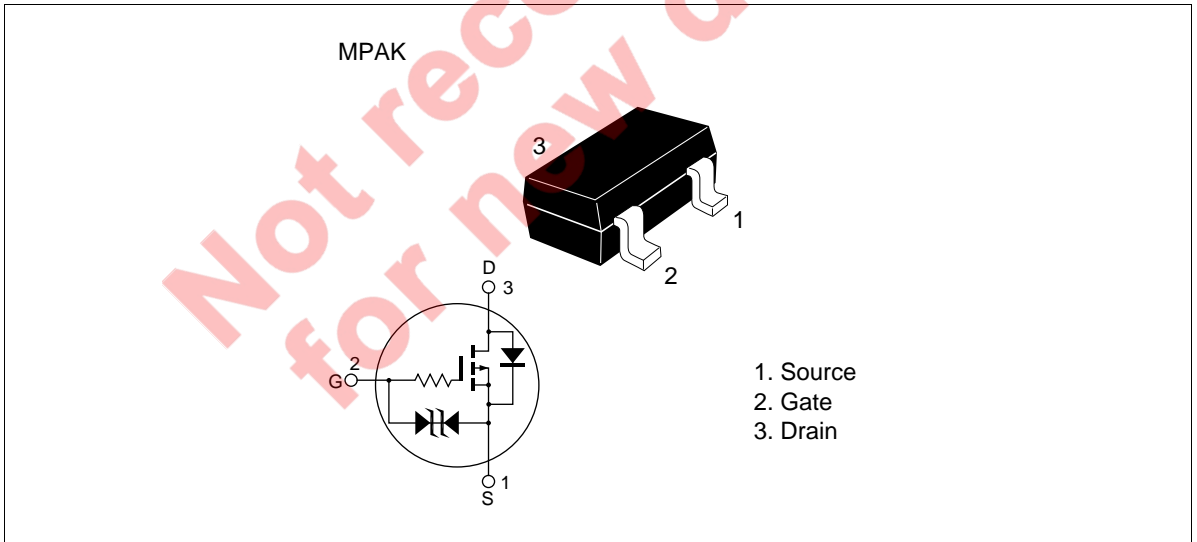
RENESAS

ADE-208-740B (Z)
3rd.Edition.
June 1999

Features

- Low on-resistance
 $R_{DS} = 2.8 \Omega$ typ. ($V_{GS} = -10 \text{ V}$, $I_D = -50 \text{ mA}$)
 $R_{DS} = 5.7 \Omega$ typ. ($V_{GS} = -4 \text{ V}$, $I_D = -50 \text{ mA}$)
- 4 V gate drive device.
- Small package (MPAK)

Outline



Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	-30	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	-100	mA
Drain peak current	$I_{D(pulse)}$ ^{Note 1}	-400	mA
Body-drain diode reverse drain current	I_{DR}	-100	mA
Channel dissipation	Pch ^{Note 2}	400	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

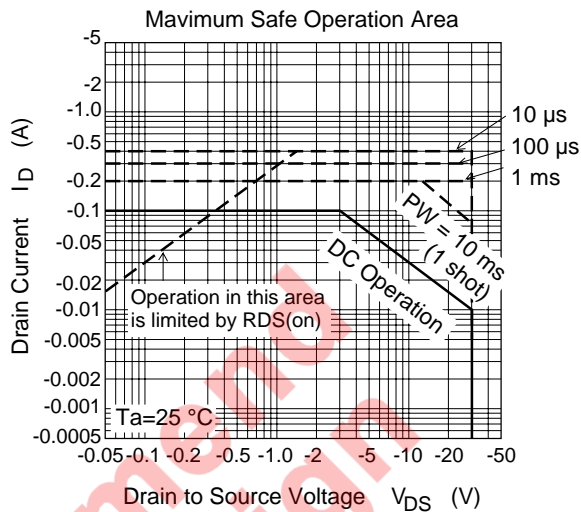
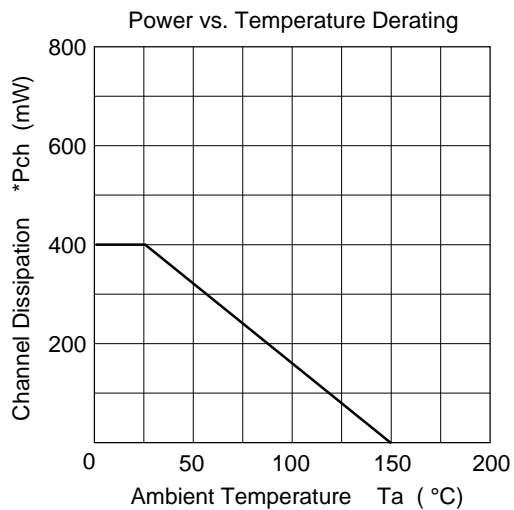
Note: 1. PW ≤ 10 μs, duty cycle ≤ 1%
 2. Value on the alumina ceramic board (12.5x20x0.7mm)

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-30	—	—	V	$I_D = -100 \mu A, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	—	V	$I_G = \pm 100 \mu A, V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	±5	μA	$V_{GS} = \pm 16 V, V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	-1	μA	$V_{DS} = -30 V, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-1.3	—	-2.3	V	$I_D = -10 \mu A, V_{DS} = -5 V$
Static drain to source on state resistance	$R_{DS(on)}$	—	2.8	3.3	Ω	$I_D = -50 mA, V_{GS} = -10 V$ ^{Note 3}
	$R_{DS(on)}$	—	5.7	7.9	Ω	$I_D = -50 mA, V_{GS} = -4 V$ ^{Note 3}
Forward transfer admittance	$ y_{fs} $	68	105	—	mS	$I_D = -50 mA, V_{DS} = -10 V$ ^{Note 3}
Input capacitance	Ciss	—	25	—	pF	$V_{DS} = -10 V$
Output capacitance	Coss	—	20	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	—	8	—	pF	f = 1 MHz
Turn-on delay time	$t_{d(on)}$	—	10	—	ns	$I_D = -50 mA, V_{GS} = -10 V$
Rise time	t_r	—	15	—	ns	$R_L = 200 \Omega$
Turn-off delay time	$t_{d(off)}$	—	40	—	ns	
Fall time	t_f	—	45	—	ns	

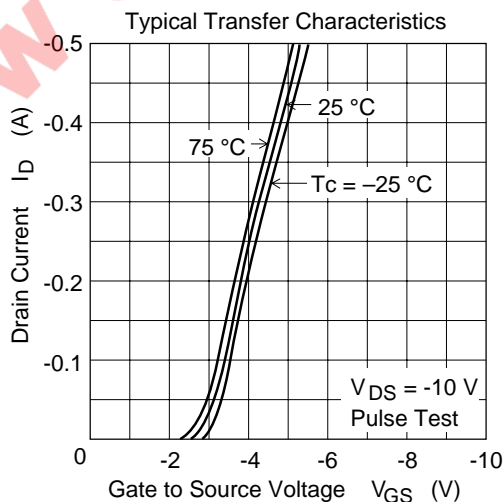
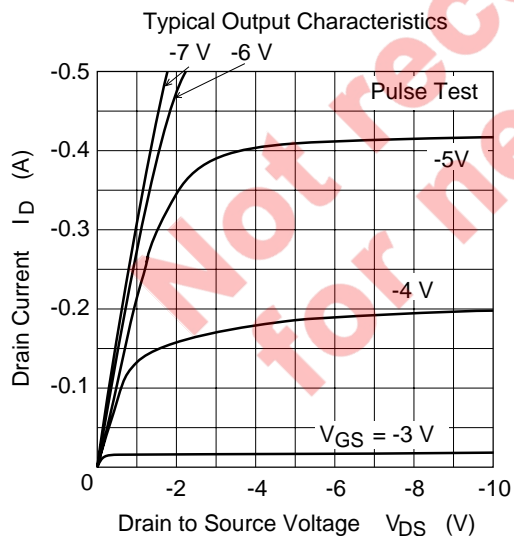
Note: 3. Pulse test
 4. Marking is AP

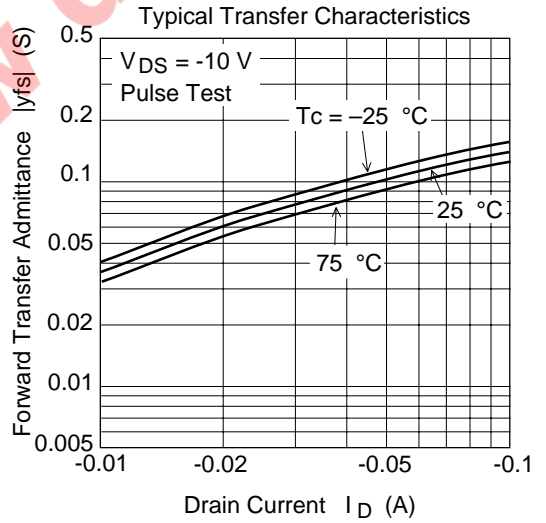
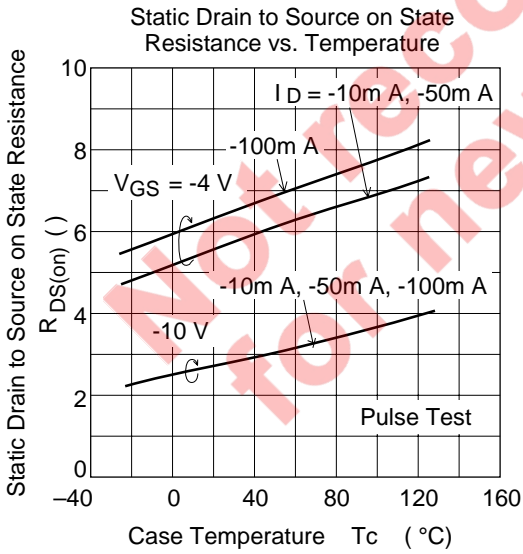
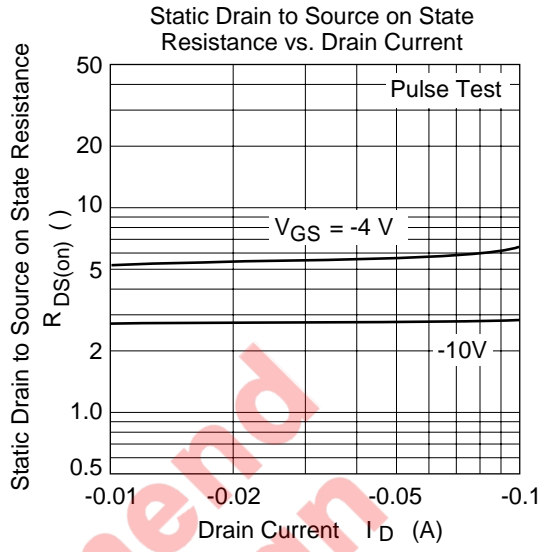
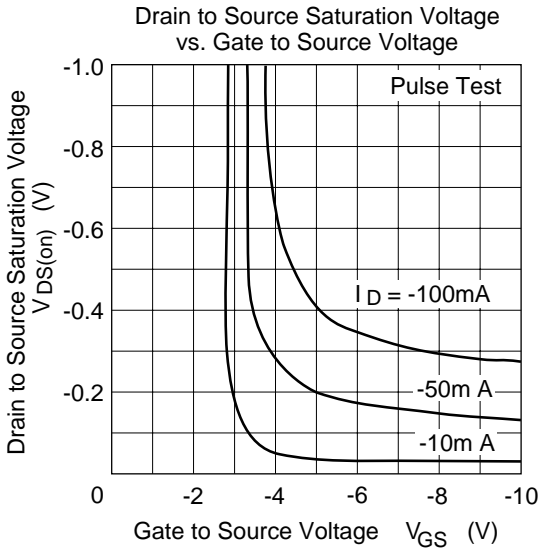
Main Characteristics

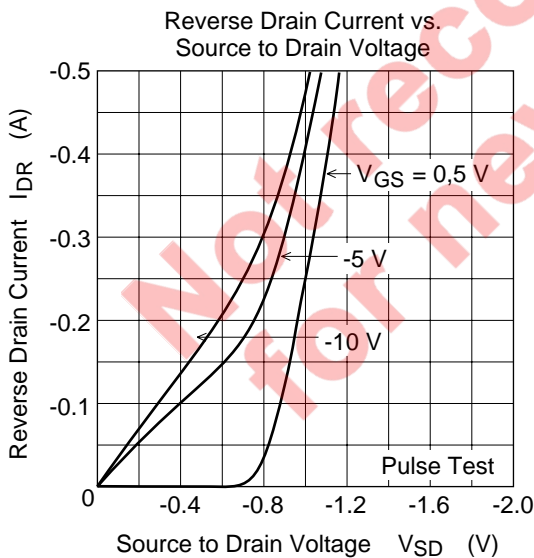
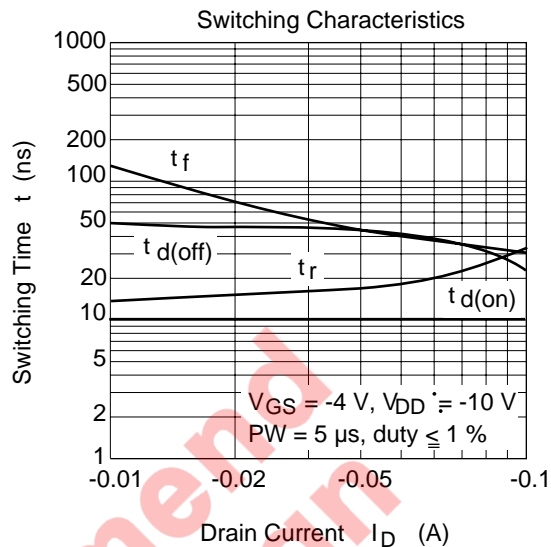
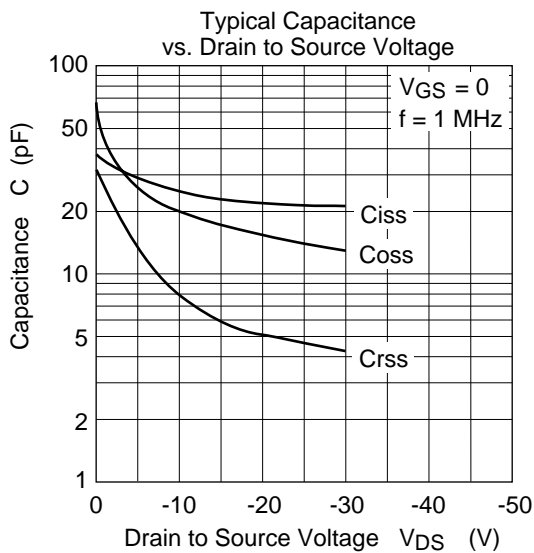


*Value on the alumina ceramic board (12.5x20x0.7mm)

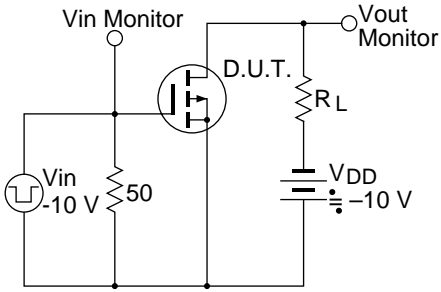
Value on the alumina ceramic board (12.5x20x0.7mm)



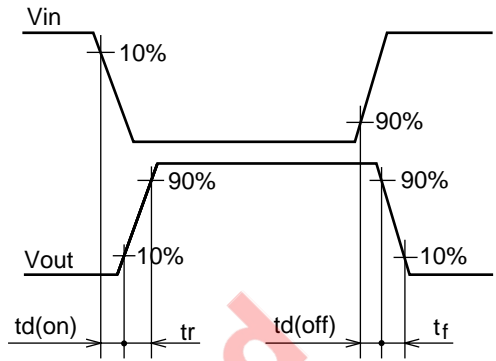




Switching Time Test Circuit



Waveforms

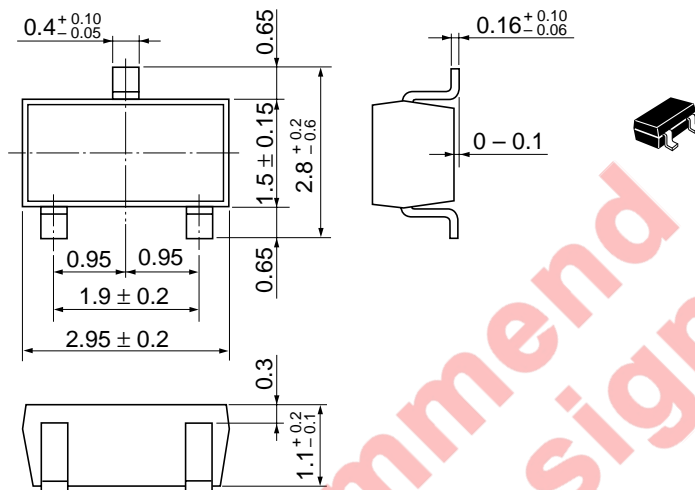


Not recommended for new design

Package Dimensions

As of January, 2001

Unit: mm



Hitachi Code	MPAK
JEDEC	—
EIAJ	Conforms
Mass (reference value)	0.011 g

Not recommend
for new design

Cautions

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